



AND LOW-DENSITY REGIONS OF  
TRANSISTOR ELEMENTS ON SINGLE  
SEMICONDUCTOR SUBSTRATE, AND  
METHOD OF MANUFACTURING SUCH  
SEMICONDUCTOR DEVICE

Inventor(s): Toshiyuki HIROTA, et al.

DOCKET NO.: 040373/0300

Fig. 2 (Prior Art)

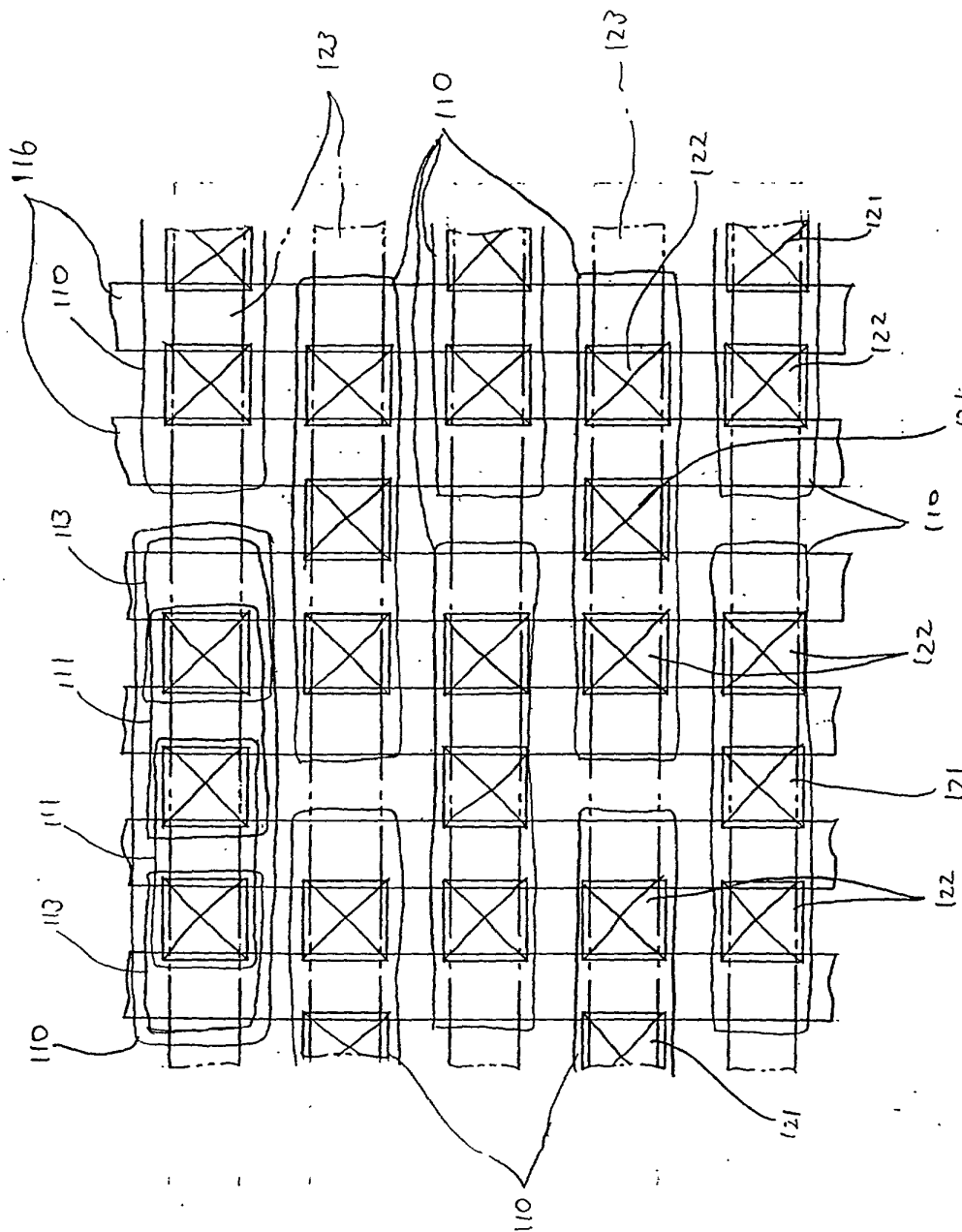
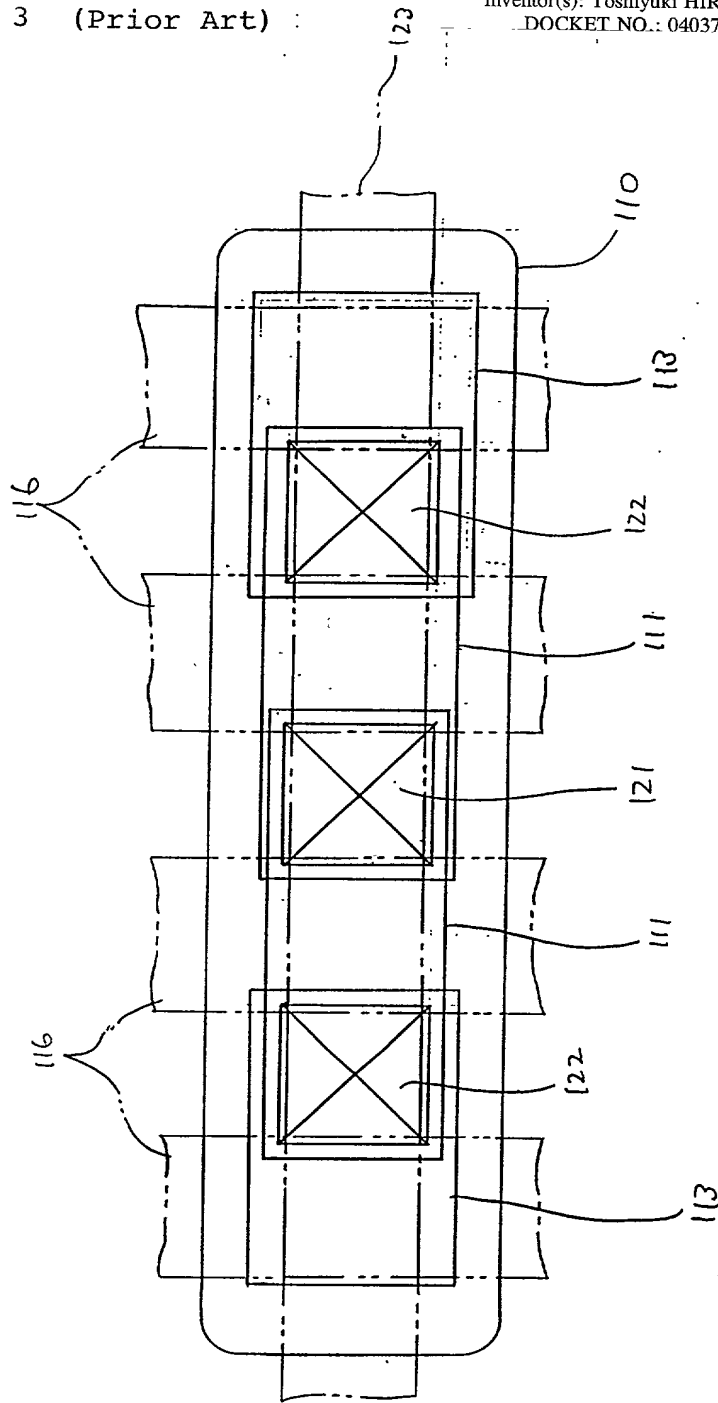


Fig. 3 (Prior Art)



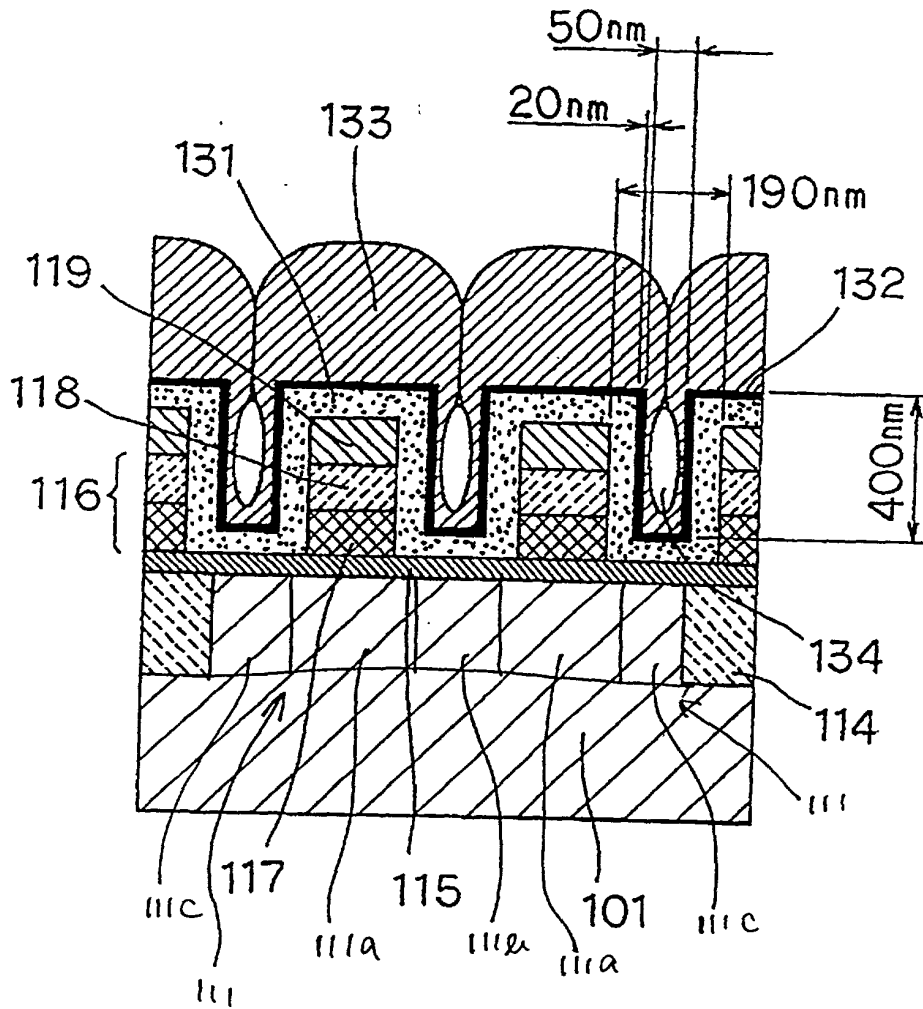


AND LOW-DENSITY REGIONS OF  
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Fig. 5 (Prior Art)



1100. SEMICONDUCTOR DEVICE WITH HIGH-  
AND LOW-DENSITY REGIONS OF  
TRANSISTOR ELEMENTS ON SINGLE  
SEMICONDUCTOR SUBSTRATE, AND  
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Fig. 6 (Prior Art)

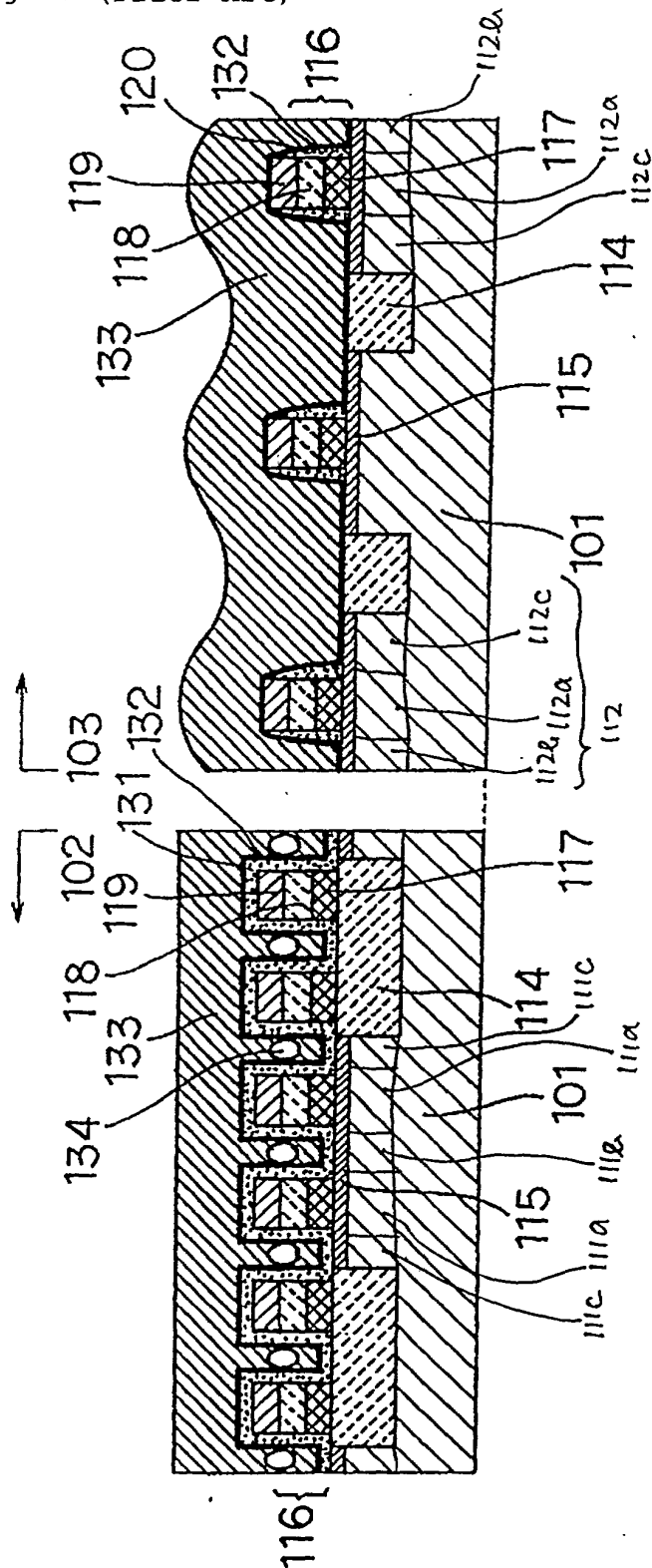


Fig. 7 (Prior Art)

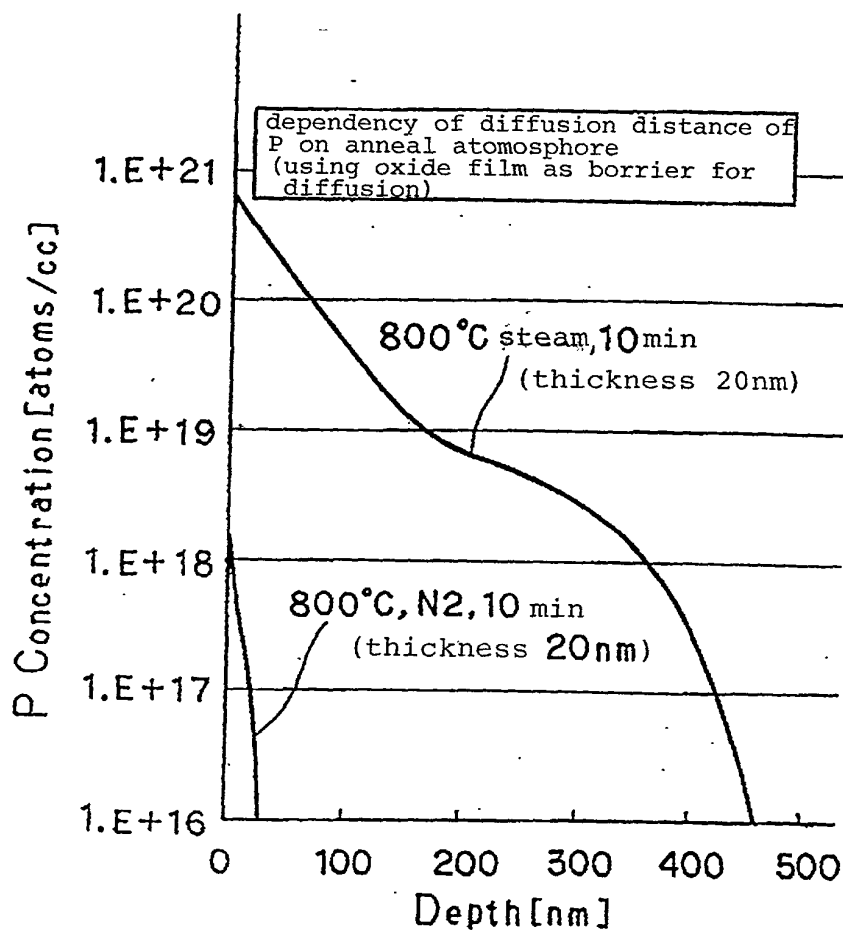


Fig. 8

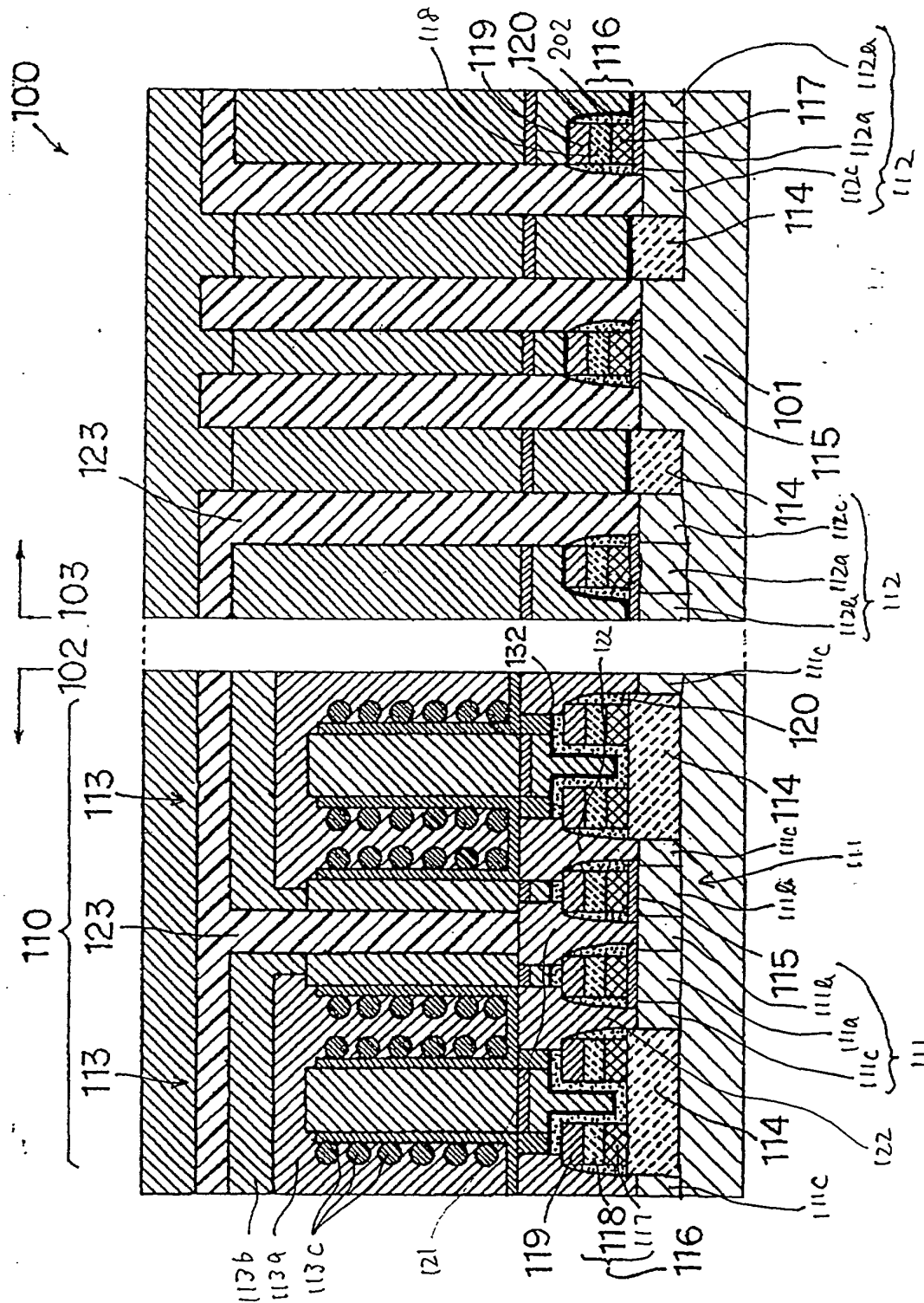




Fig. 9A

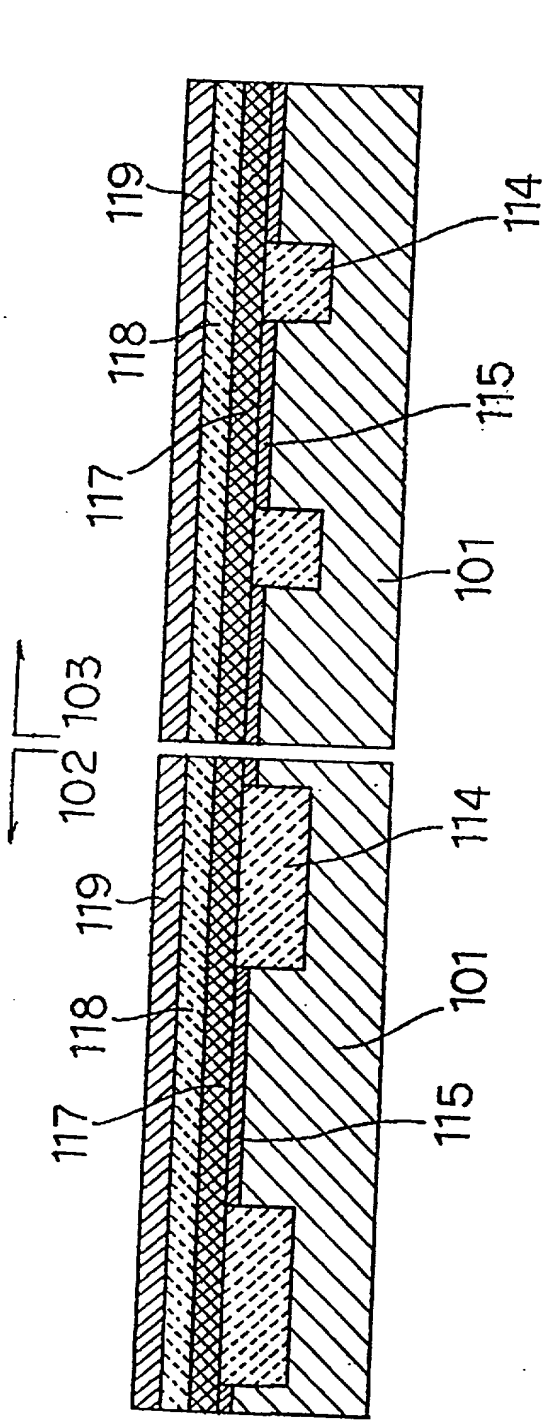
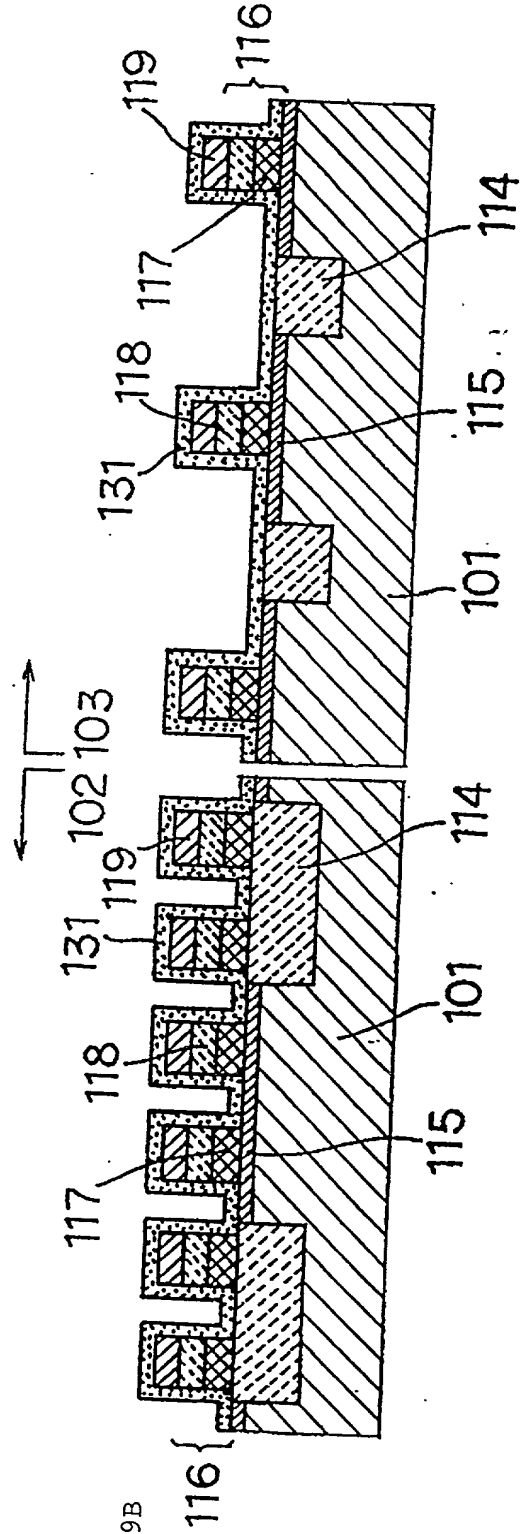
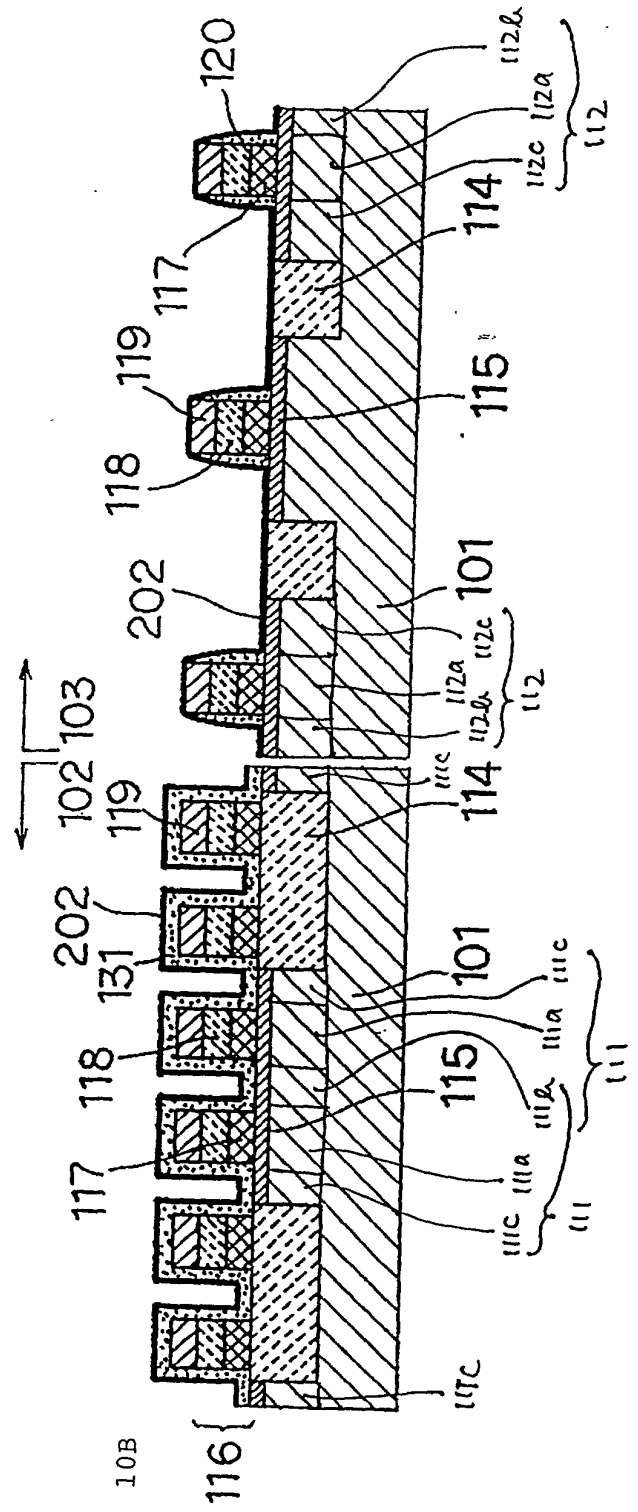
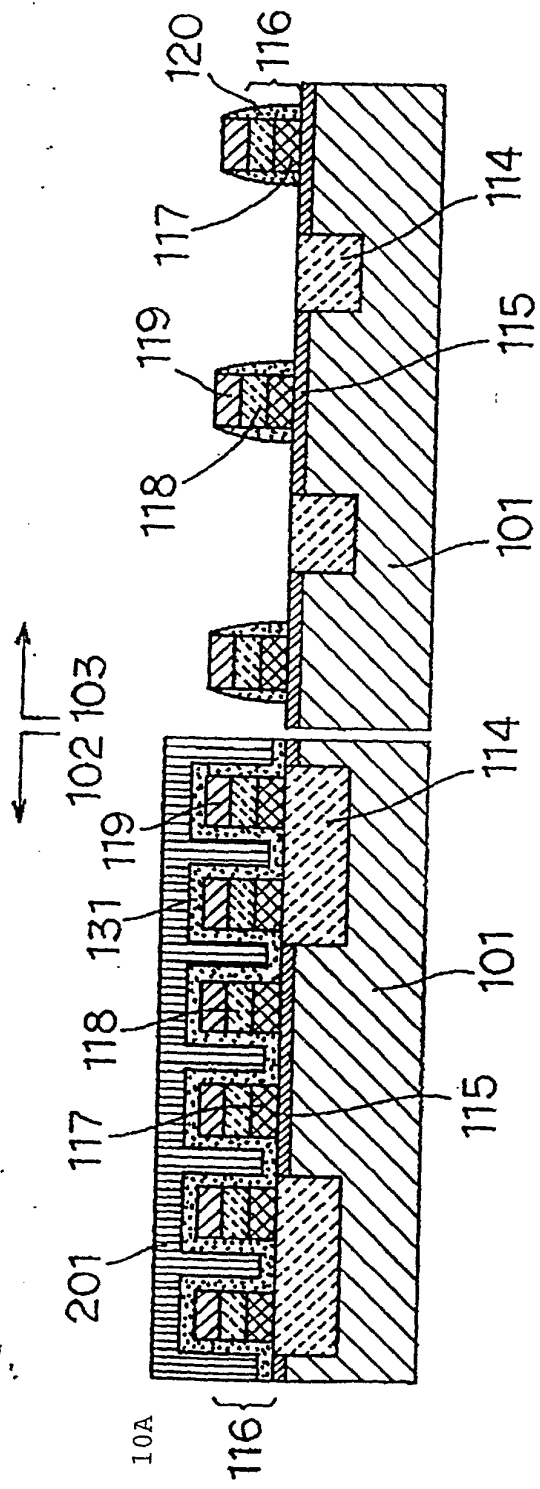


Fig. 9B









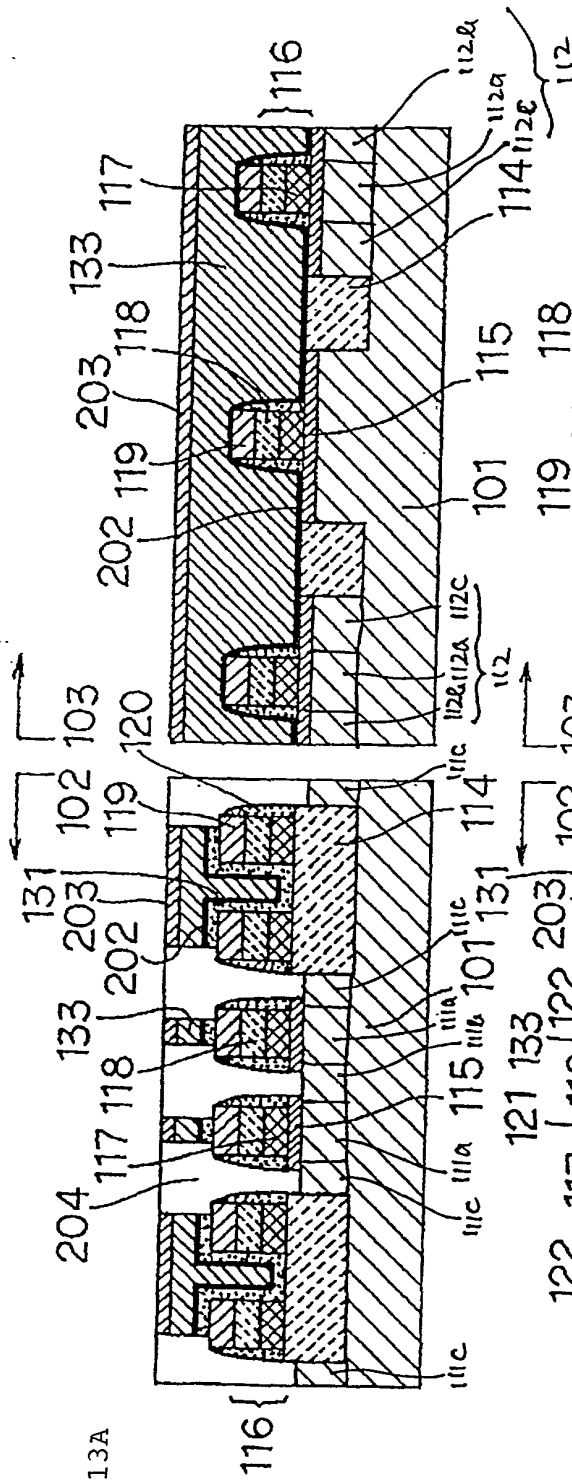


Fig. 13A

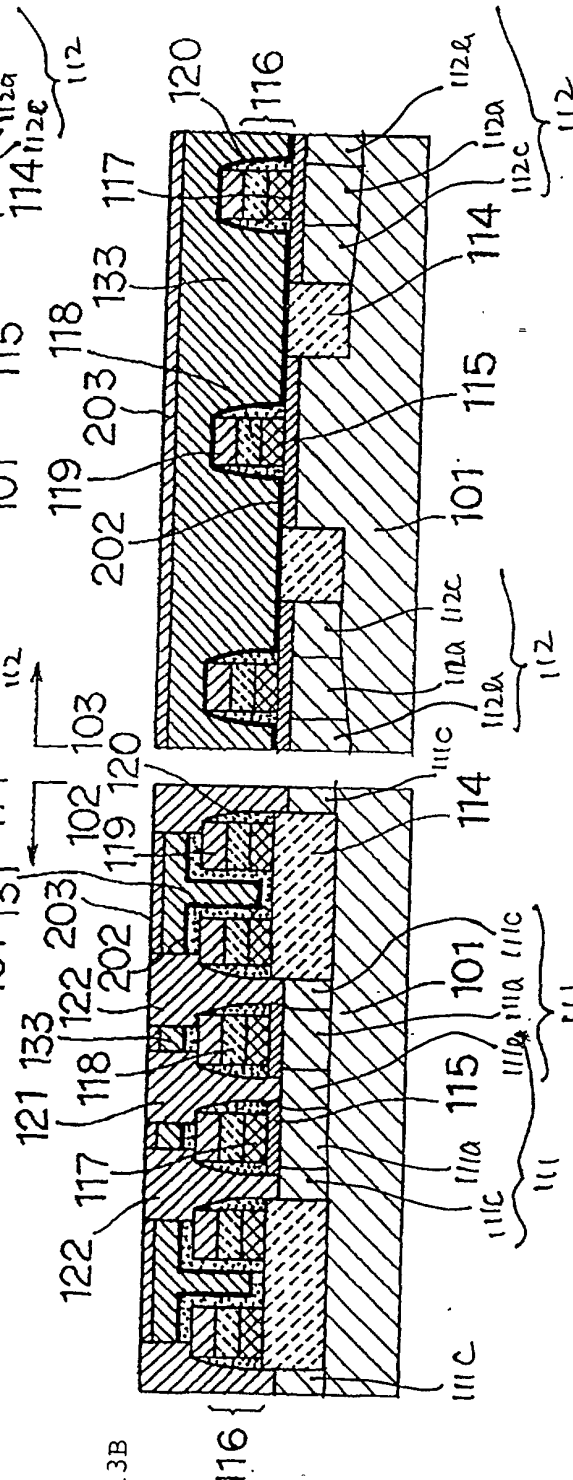


Fig. 13B

Fig. 14

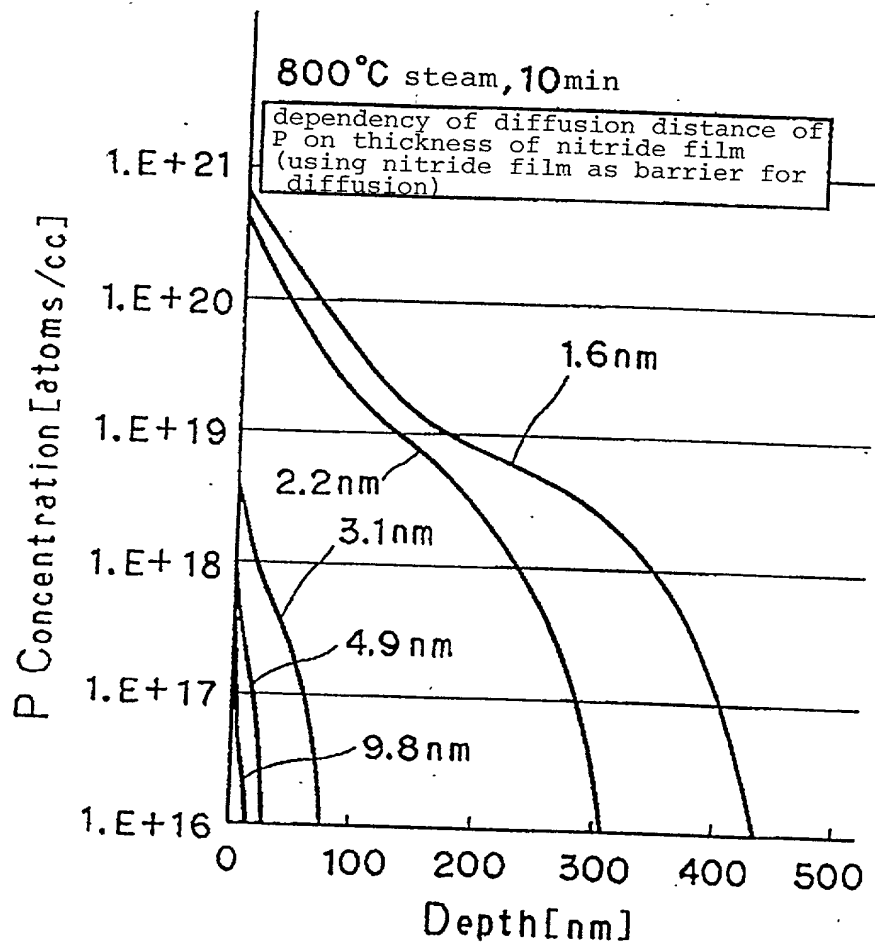


Fig. 15

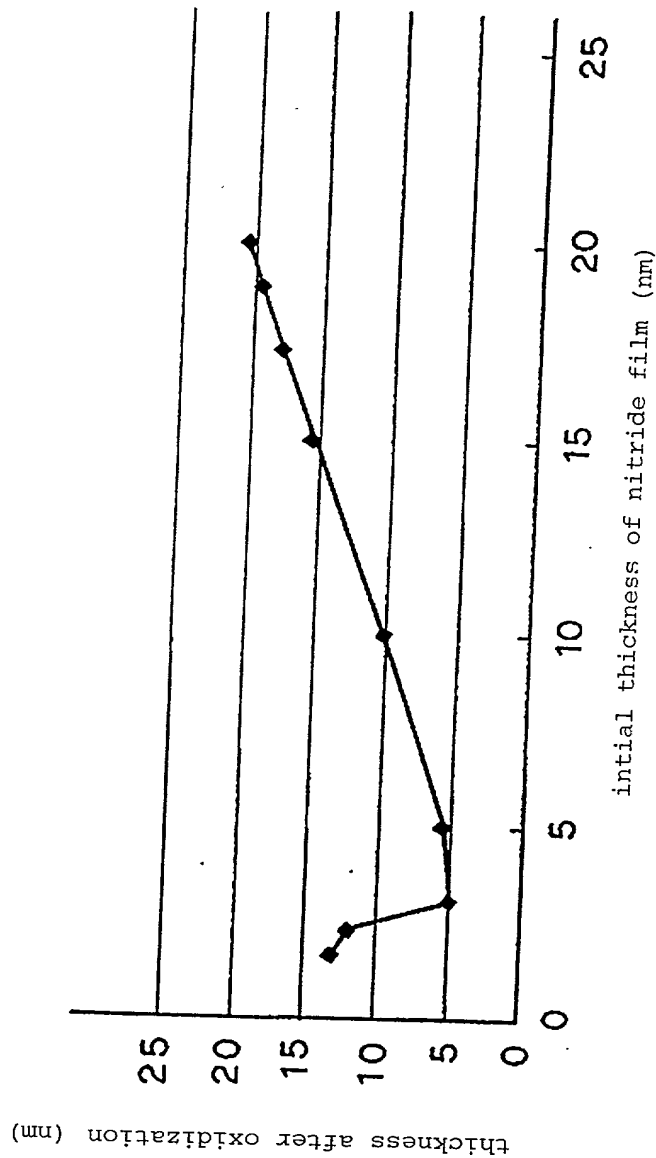
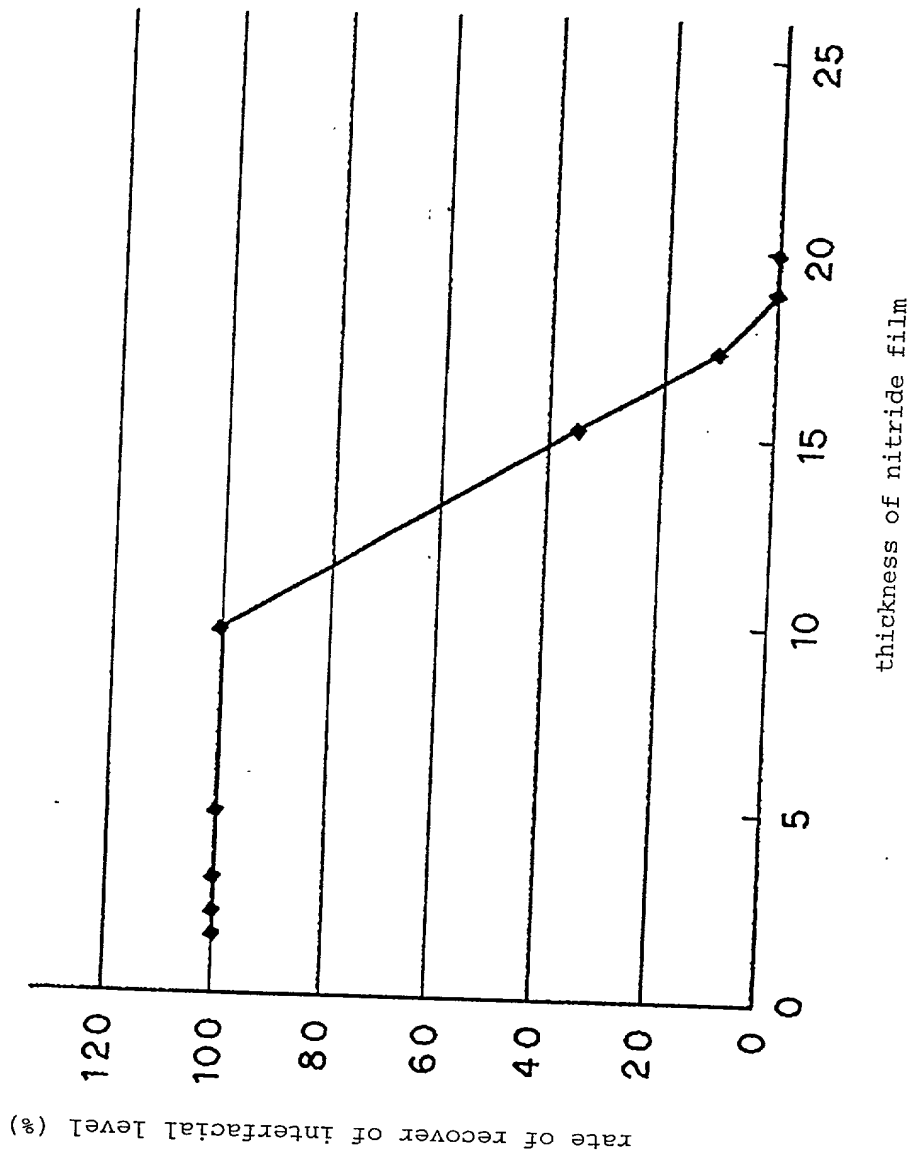


Fig. 16







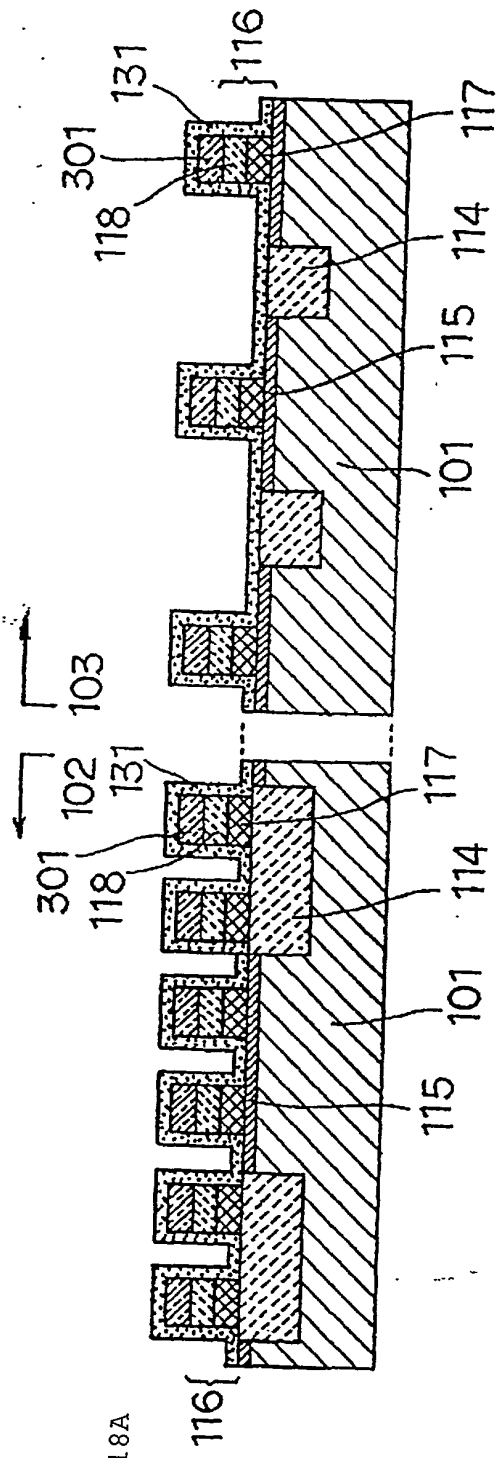


Fig. 18A

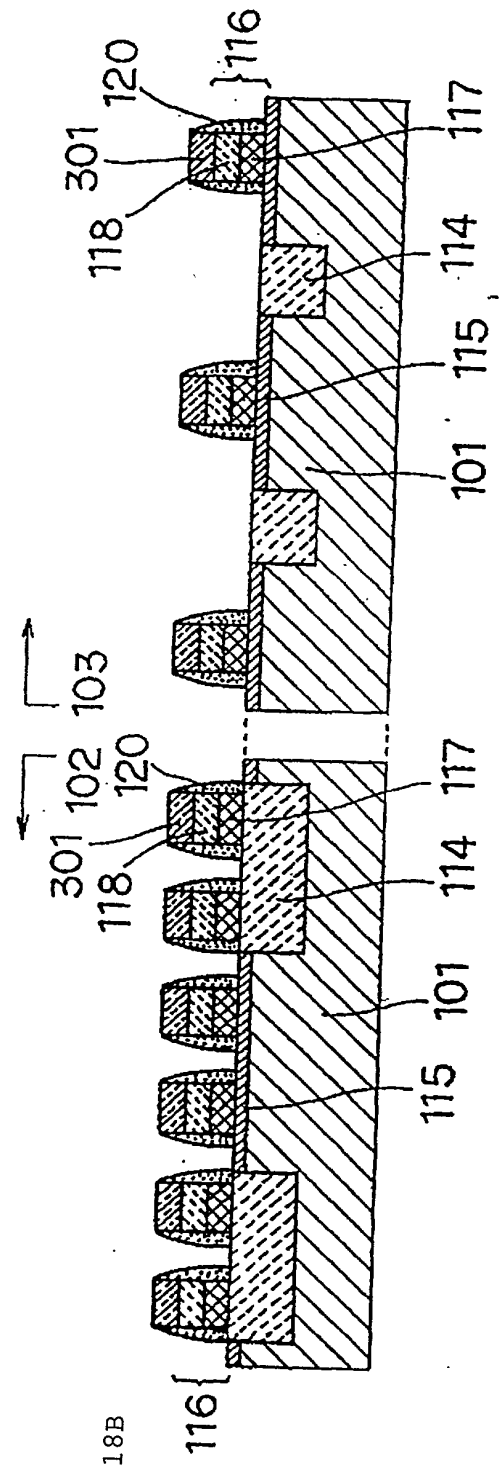


Fig. 18B

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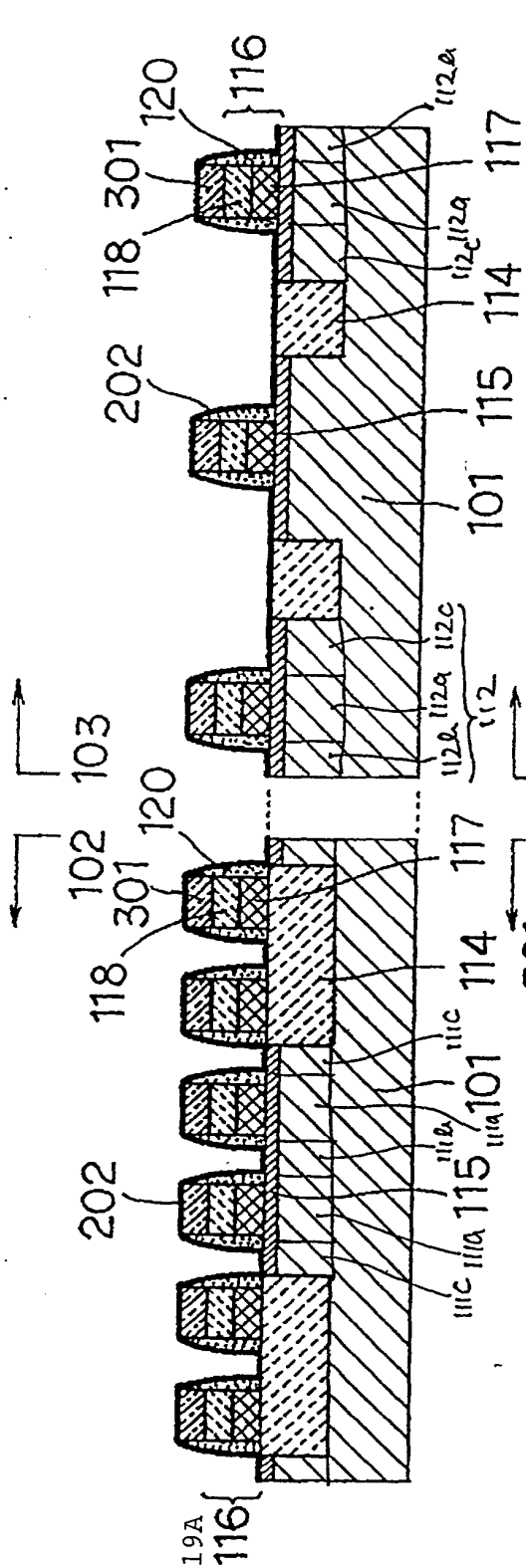


Fig. 19A

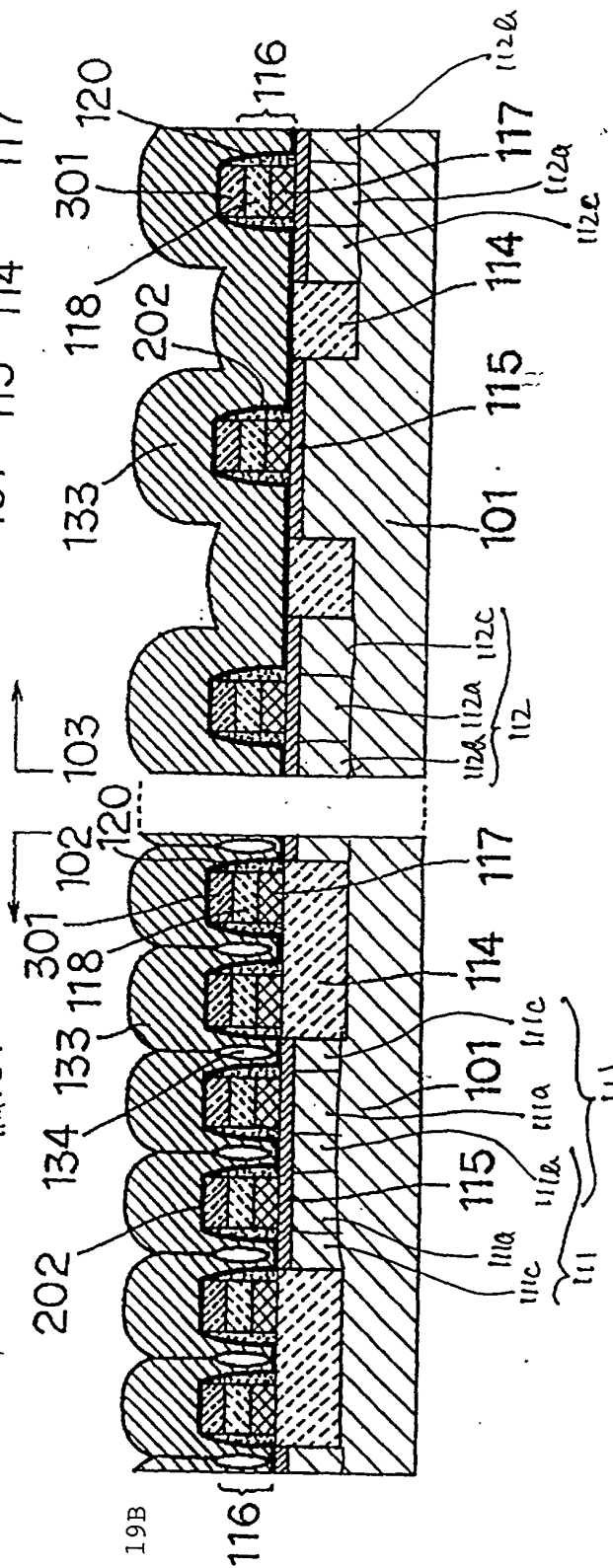


Fig. 19B

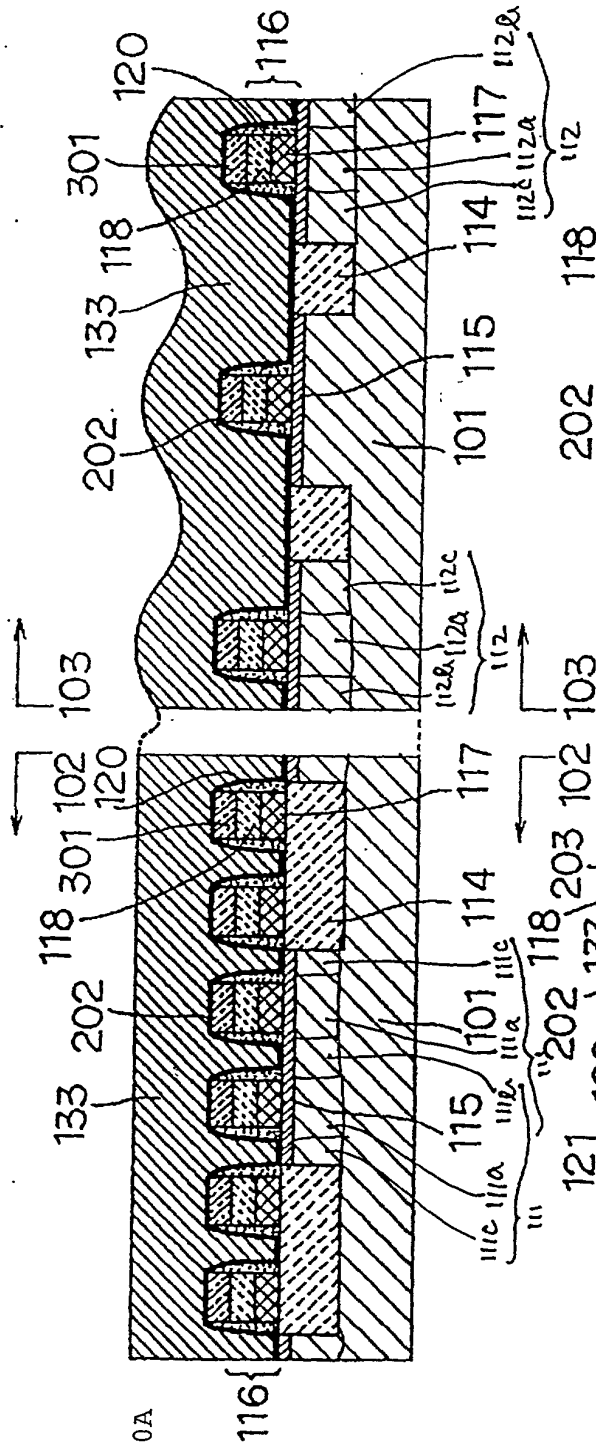


Fig. 20A

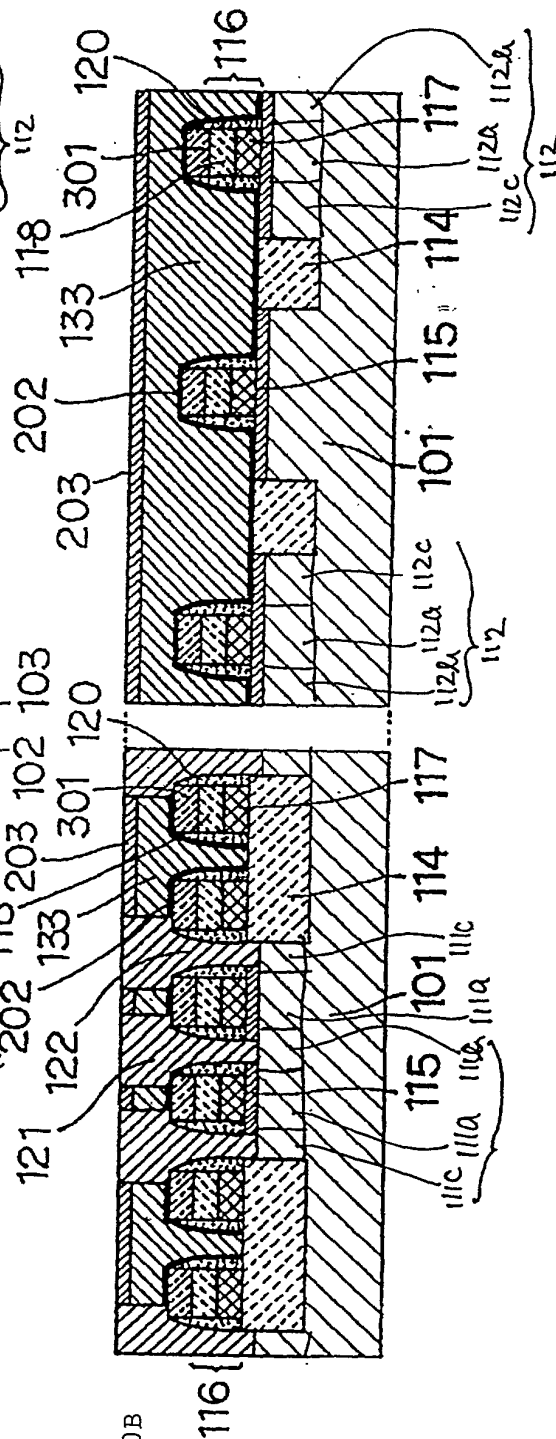


Fig. 20B



Fig. 22

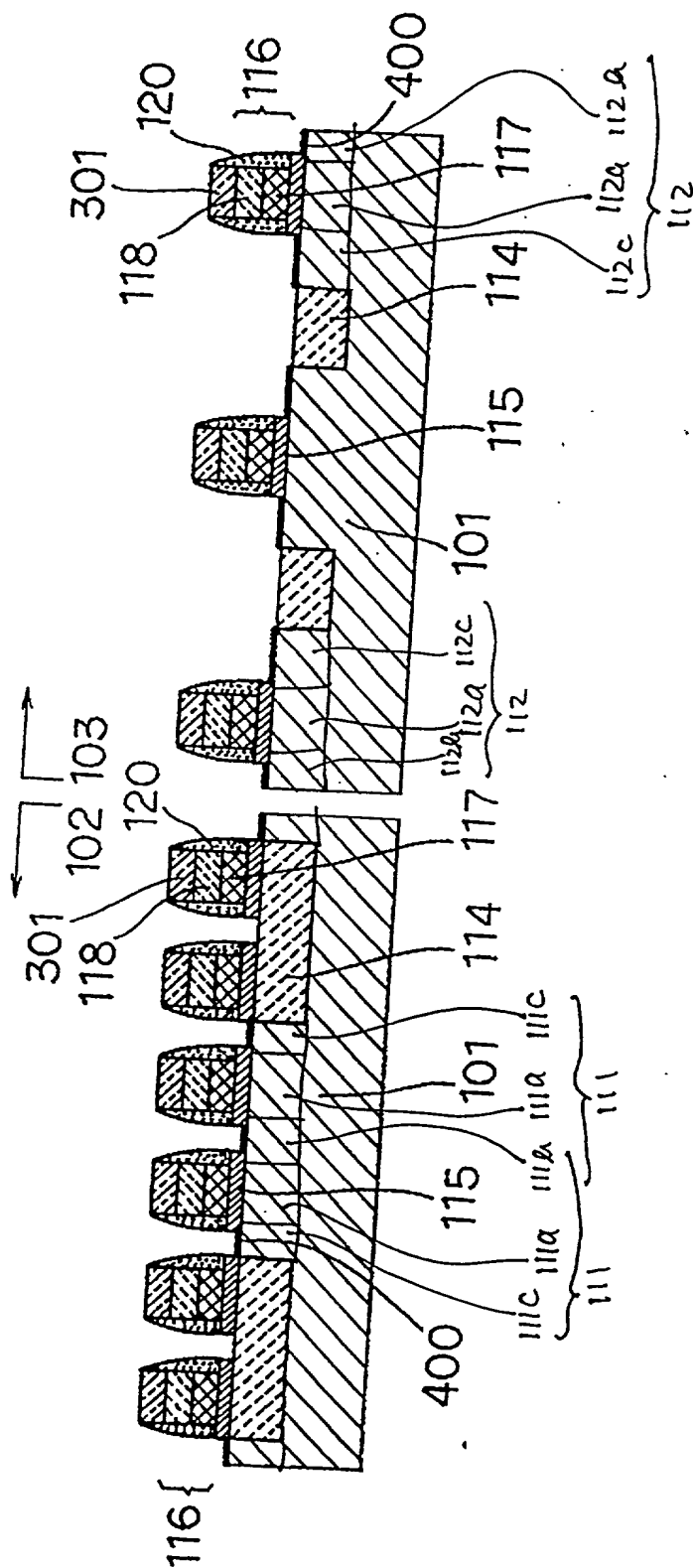


Fig. 23

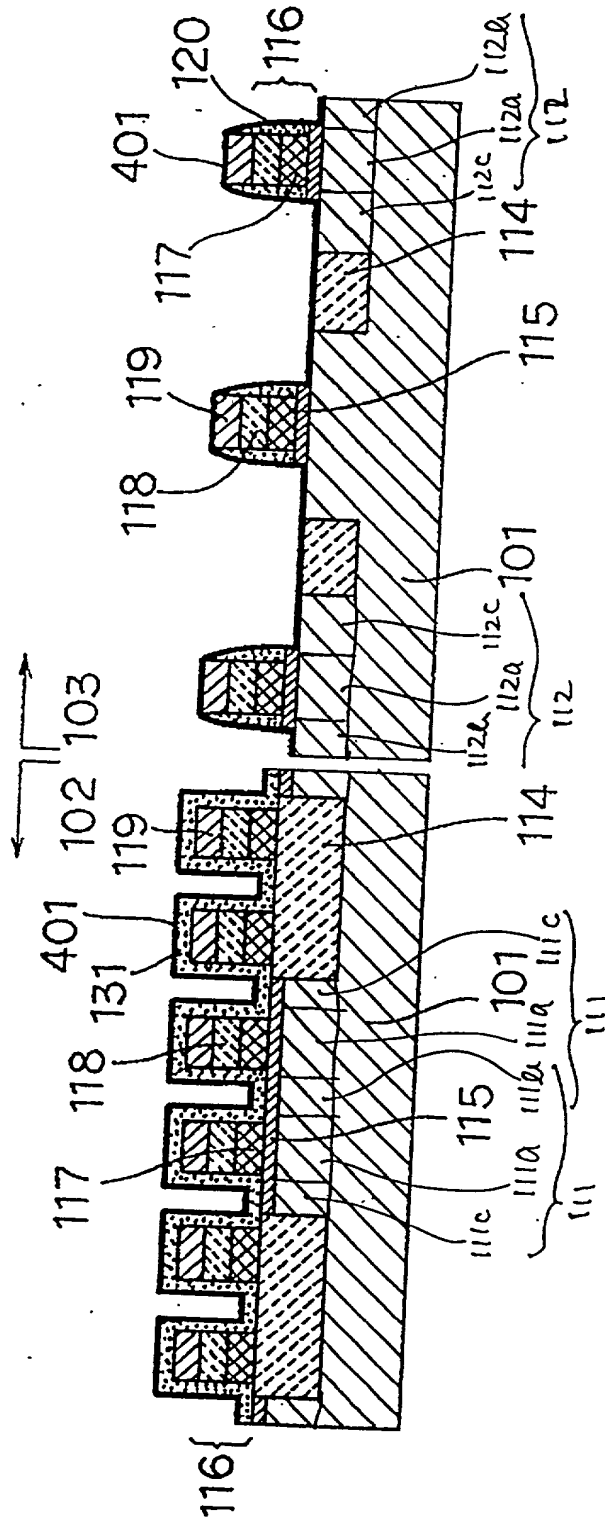


Fig. 24

